

General Description:

Schottky Barrier Diodes make use of the rectification effect of a metal to silicon barrier. They are ideally suited for high frequency rectification in switching regulators & converters. This device offers a low forward voltage performance in a power surface mount package in applications where size and weight are critical.

Features:

- Compact surface mount package with J-bend leads (SMB).
- 1.5 Watt Power Dissipation package.
- 1.0 Ampere, forward voltage less than 395 mv

Ordering:

- 13 inch reel (330 mm); 12 mm Tape; 3,000 units per reel.

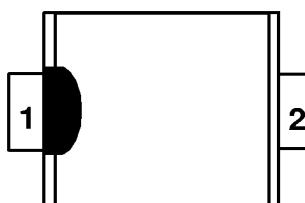
Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Parameter	Value	Units
Storage Temperature	-65 to +150	°C
Maximum Junction Temperature	-65 to +125	°C
Repetitive Peak Reverse Voltage (V _{RRM})	30	V
Average Rectified Forward Current (T _L = 120°C)	1.0	A
(T _L = 110°C)	2.0	A
Surge Non Repetitive Forward Current (Half wave, single phase, 60 Hz)	40	A
Junction to Case for Thermal Resistance (R _{θJL})	12	°C/W

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

SMB Package
(DO-214AA)

Top Mark: 1BL3

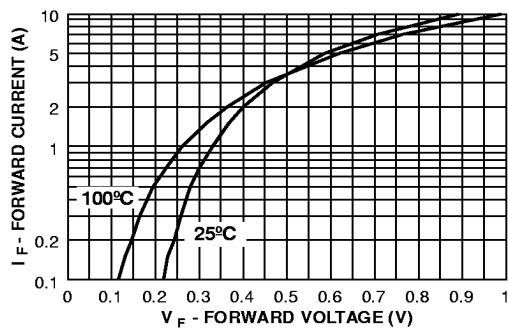
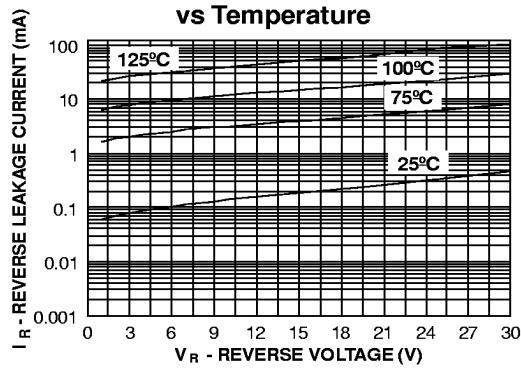
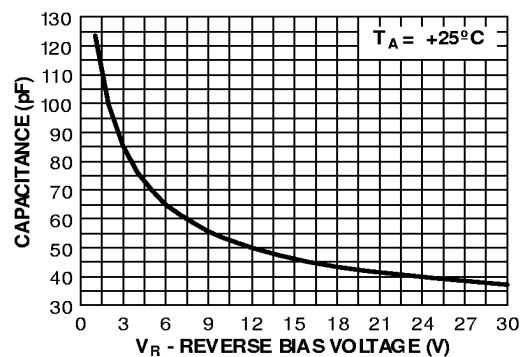


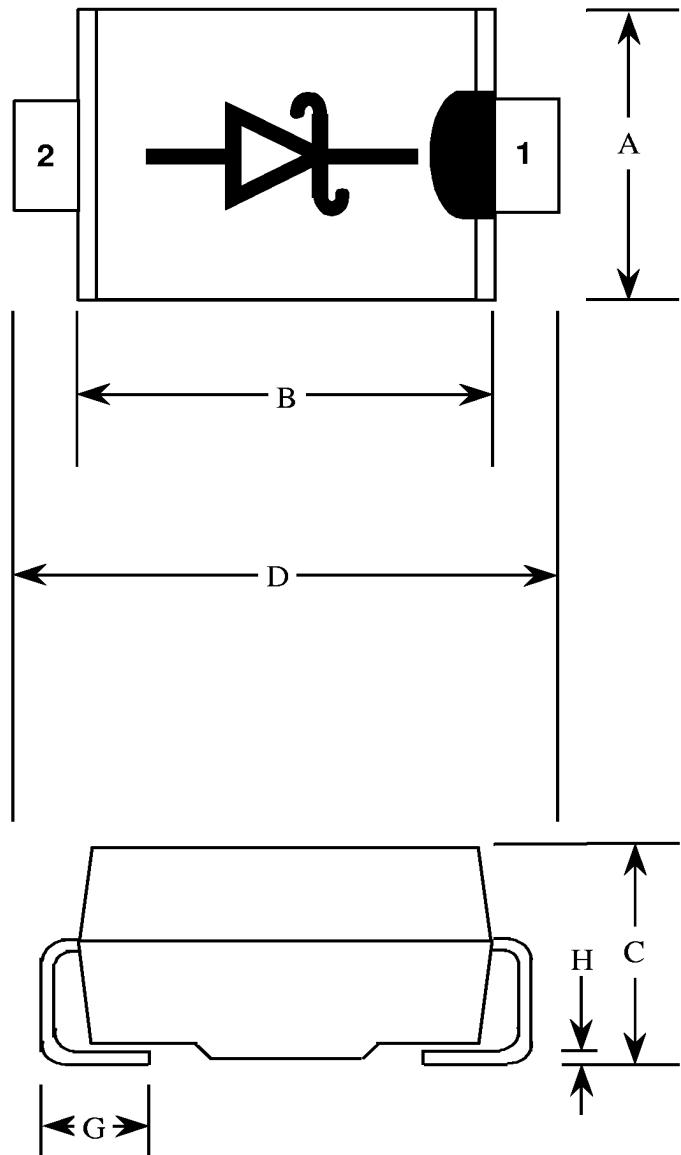
Actual Size

Electrical Characteristics

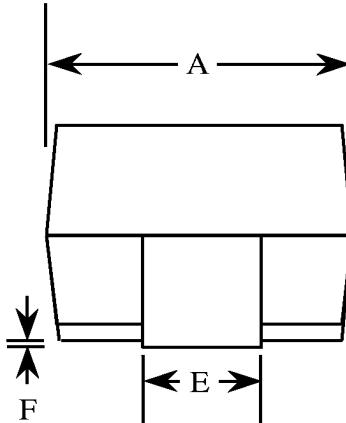
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SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
I _R	Reverse Leakage Current PW 300 us, \leq 2% Duty Cycle		1.0 10	mA mA	V _R = 30 V; T _j = 25°C V _R = 30 V; T _j = 100°C
V _F	Forward Voltage PW 300 us, \leq 2% Duty Cycle		395 445	mV mV	I _F = 1.0 A; T _j = 25°C I _F = 2.0 A; T _j = 25°C

Forward Voltage vs Temperature**Reverse Leakage Current vs Temperature****Capacitance vs. Reverse Bias Voltage**



Actual Size DIM	MIN (mils)	MAX (mils)	MIN (mm)	MAX (mm)
A	130	155	3.30	3.94
B	160	180	4.06	4.57
C	79	103	2.00	2.62
D	205	220	5.21	5.59
E	77	87	1.96	2.21
F	4	8	0.10	0.20
G	30	60	0.76	1.52
H	6	12	0.15	0.31



SMB PACKAGE
PACKAGE CODE = (MB)
Fairchild Semiconductor's Criteria